

NJ132 Process

Silicon Junction Field-Effect Transistor

- High Speed Switch
- Low-Noise Amplifier

Absolute maximum ratings at TA = 25 °C

Gate Current, Ig	10 mA
Operating Junction Temperature, Tj	+150°C
Storage Temperature, Ts	– 65°C to +175°C

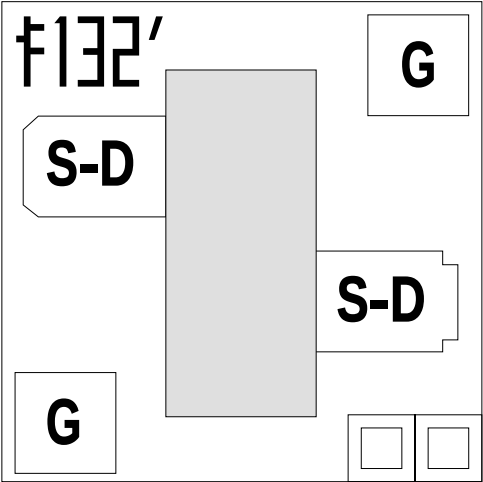
Devices in this Databook based on the NJ132 Process.

Datasheet

2N4391, 2N4392
2N4393
2N4856, 2N4857
2N4858, 2N4859
2N4860, 2N4861
2N4856A, 2N4857A
2N4858A, 2N4859A

Datasheet

2SK113
1FN113
2N4860A, 2N4861A
J111, J112
J113



Die Size = 0.022" X 0.022"
All Bond Pads = 0.004" Sq.
Substrate is also Gate.

www.DataSheet4U.com

At 25°C free air temperature:		NJ132 Process					
		Min	Typ	Max	Unit	Test Conditions	
Gate Source Breakdown Voltage	V _{(BR)GSS}	– 30	– 45		V	I _G = – 1 μA, V _{DS} = 0V	
Reverse Gate Leakage Current	I _{GSS}		– 10	– 100	pA	V _{GS} = – 20V, V _{DS} = 0V	
Drain Saturation Current (Pulsed)	I _{DSS}	10		150	mA	V _{DS} = 20V, V _{GS} = 0V	
Gate Source Cutoff Voltage	V _{GS(OFF)}	– 0.5		– 7	V	V _{DS} = 20V, I _D = 1 nA	
Dynamic Electrical Characteristics							
Drain Source ON Resistance	r _{ds(on)}		25		Ω	I _D = 1 mA, V _{GSS} = 0V	f = 1 kHz
Input Capacitance	C _{iss}		12		pF	V _{DS} = 20V, V _{GS} = 0V	f = 1 MHz
Feedback Capacitance	C _{iss}		2.5		pF	V _{DS} = 0V, V _{GS} = – 10V	f = 1 MHz
Turn On Delay Time	t _{d(on)}		6		ns	V _{DD} = – 10V, I _D = 10 mA R _L = 10V, V _{GS(ON)} = 0V V _{GS(OFF)} = – 6V	
Rise Time	t _r		5		ns		
Turn Off Delay Time	t _{d(off)}		50		ns		

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